

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a semiconductor substrate;  
an insulating film formed on said semiconductor substrate; a  
5 ferroelectric capacitor having a lower electrode, a  
ferroelectric film and an upper electrode which are stacked  
sequentially on the insulating film; a first hydrogen barrier  
film; a first inter-layer insulating film covering said  
ferroelectric capacitor; and a second inter-layer  
10 insulating film stacked on the first inter-layer insulating film,  
the first hydrogen barrier film being interposed between the first  
and second interlayer insulating films is proposed.